Fei Zhou

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/12052358/publications.pdf

Version: 2024-02-01

47	1,205	304602	377752
papers	citations	22 h-index	34 g-index

47	47	47	1040
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Review of Recently Progress on Neural Electronics and Memcomputing Applications in Intrinsic SiOx-Based Resistive Switching Memory. , 2018, , .		2
2	Dynamic conductance characteristics in HfO_x-based resistive random access memory. RSC Advances, 2017, 7, 12984-12989.	1.7	32
3	A synaptic device built in one diodeâ€“one resistor (1Dâ€“1R) architecture with intrinsic SiOx-based resistive switching memory. ChemistrySelect, 2016, 1, .	0.7	0
4	Resistive switching characteristics and mechanisms in silicon oxide memory devices. ChemistrySelect, 2016, 1, .	0.7	2
5	Study of self-compliance behaviors and internal filament characteristics in intrinsic SiOx-based resistive switching memory. Applied Physics Letters, 2016, 108, .	1.5	35
6	Demonstration of Synaptic Behaviors and Resistive Switching Characterizations by Proton Exchange Reactions in Silicon Oxide. Scientific Reports, 2016, 6, 21268.	1.6	84
7	A study of the interfacial resistive switching mechanism by proton exchange reactions on the SiO_x layer. Physical Chemistry Chemical Physics, 2016, 18, 700-703.	1.3	19
8	Bidirectional voltage biased implication operations using SiOx based unipolar memristors. Applied Physics Letters, 2015, 107, 183501.	1.5	22
9	Electroforming and resistive switching in silicon dioxide resistive memory devices. RSC Advances, 2015, 5, 21215-21236.	1.7	59
10	Stabilization of multiple resistance levels by current-sweep in SiOx-based resistive switching memory. Applied Physics Letters, 2015, 106, .	1.5	41
11	Study of SiO<inf>x</inf>-based resistive switching memory (ReRAM) in integrated one diode — One resistor (1D-1R) architecture. , 2015, , .		3
12	Discussion on device structures and hermetic encapsulation for SiOx random access memory operation in air. Applied Physics Letters, 2014, 105, .	1.5	17
13	Intrinsic SiOx-based unipolar resistive switching memory. II. Thermal effects on charge transport and characterization of multilevel programing. Journal of Applied Physics, 2014, 116, .	1.1	83
14	Characterization of external resistance effect and performance optimization in unipolar-type SiOx-based resistive switching memory. Applied Physics Letters, 2014, 105, .	1.5	16
15	Nonplanar InGaAs Gate Wrapped Around Field-Effect Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2332-2337.	1.6	16
16	III-V Gate-wrap-around field-effect-transistors with high-k gate dielectrics. , 2014, , .		3
17	Intrinsic SiOx-based unipolar resistive switching memory. I. Oxide stoichiometry effects on reversible switching and program window optimization. Journal of Applied Physics, 2014, 116, .	1.1	55
18	Oxygen-induced bi-modal failure phenomenon in SiOx-based resistive switching memory. Applied Physics Letters, 2013, 103, 033521.	1.5	30

#	Article	IF	Citations
19	Effects of sidewall etching on electrical properties of SiOx resistive random access memory. Applied Physics Letters, 2013, 103, 213505.	1.5	20
20	Comprehensive trap-level study in SiO<inf>x</inf>-based resistive switching memory. , 2013, , .		9
21	Investigation of edge- and bulk-related resistive switching behaviors and backward-scan effects in SiO_x-based resistive switching memory. Applied Physics Letters, 2013, 103, 193508.	1.5	26
22	Random Process of Filamentary Growth and Localized Switching Mechanism in Resistive Switching of SiO_xThin Films. ECS Journal of Solid State Science and Technology, 2012, 1, P148-P151.	0.9	9
23	HfO2 dielectrics engineering using low power SF6 plasma on InP and In0.53Ga0.47As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2012, 100, 243508.	1.5	6
24	Effect of hydrogen/deuterium incorporation on electroforming voltage of SiOx resistive random access memory. Applied Physics Letters, 2012, 101, .	1.5	20
25	Understanding the resistive switching characteristics and mechanism in active SiOx-based resistive switching memory. Journal of Applied Physics, 2012, 112, .	1.1	72
26	Sub-50-nm $hbox{In}_{0.7}hbox{Ga}_{0.3}hbox{As}$ MOSFETs With Various Barrier Layer Materials. IEEE Electron Device Letters, 2012, 33, 32-34.	2.2	51
27	Channel Thickness Dependence of InGaAs Quantum-Well Field-Effect Transistors With High- $kappa$ Gate Dielectrics. IEEE Electron Device Letters, 2012, 33, 1255-1257.	2.2	10
28	Memory switching properties of e-beam evaporated SiOx on N++ Si substrate. Applied Physics Letters, 2012, 100, .	1.5	48
29	Tristate Operation in Resistive Switching of $ hbox{SiO}_{2}$ Thin Films. IEEE Electron Device Letters, 2012, 33, 1702-1704.	2.2	25
30	Study of polarity effect in SiO_x-based resistive switching memory. Applied Physics Letters, 2012, 101, 052111.	1.5	47
31	Study of SiO<inf>x</inf>-based complementary resistive switching memristor. , 2012, , .		9
32	Effects of SF₆ plasma treatment on electrical characteristics of TaN-Al₂O₃-InP metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2012, 101, 063505.	1.5	2
33	Optimization of Fluorine Plasma Treatment for Interface Improvement on HfO2/In0.53Ga0.47As MOSFETs. Applied Sciences (Switzerland), 2012, 2, 233-244.	1.3	6
34	Physical and Electrical Analysis of Post-$ hbox{HfO}_{2}$ Fluorine Plasma Treatment for the Improvement of $hbox{In}_{0.53}hbox{Ga}_{0.47}hbox{As}$ MOSFETs' Performance. IEEE Transactions on Electron Devices, 2012, 59, 139-144.	1.6	13
35	High-k InGaAs metal-oxide-semiconductor field-effect-transistors with various barrier layer materials. Applied Physics Letters, 2011, 99, 033507.	1.5	19
36	InAs inserted InGaAs buried channel metal-oxide-semiconductor field-effect-transistors with atomic-layer-deposited gate dielectric. Applied Physics Letters, 2011, 98, .	1.5	36

#	Article	IF	Citations
37	Effect of indium concentration on InGaAs channel metal-oxide-semiconductor field-effect transistors with atomic layer deposited gate dielectric. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	3
38	Impact of SF6 plasma treatment on performance of TaNâ€“HfO2â€“InP metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2011, 98, 043506.	1.5	10
39	Improved Electrical Properties of HfO2-Based Gate Dielectrics on InP Substrate Using Al2O3/HfO2 and SF6 Plasma Treatment. Electrochemical and Solid-State Letters, 2011, 14, H291.	2.2	14
40	Improving the on-current of In0.7Ga0.3As tunneling field-effect-transistors by p++/n+ tunneling junction. Applied Physics Letters, 2011, 98, .	1.5	26
41	Effects of barrier layers on device performance of high mobility In0.7Ga0.3As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, .	1.5	66
42	Fluorinated HfO2 gate dielectric engineering on In0.53Ga0.47As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, .	1.5	24
43	Effects of fluorine incorporation into HfO2 gate dielectrics on InP and In0.53Ga0.47As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, 253502.	1.5	24
44	Effects of Fluorine Incorporation on the Electrical Properties of Atomic-Layer-Deposited Al[sub 2]O[sub 3] Gate Dielectric on InP Substrate. Journal of the Electrochemical Society, 2010, 157, G71.	1.3	11
45	Effects of InP barrier layer thicknesses and different ALD oxides on device performance of In<inf>0.7</inf>Ga<inf>0.3</inf>As MOSFETs. , 2010, , .		5
46	Improved electrical characteristics of TaN/Al2O3/In0.53Ga0.47As metal-oxide-semiconductor field-effect transistors by fluorine incorporation. Applied Physics Letters, 2009, 95, 013501.	1.5	33
47	Effects of gate-first and gate-last process on interface quality of In0.53Ga0.47As metal-oxide-semiconductor capacitors using atomic-layer-deposited Al2O3 and HfO2 oxides. Applied Physics Letters, 2009, 95, .	1.5	42